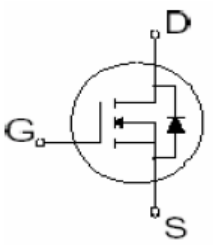
Taiwan Goodark Technology Co.,Ltd

SSFP10N65

StarMOS^T Power MOSFET

- Extremely high dv/dt capability
- Low Gate Charge Qg results in Simple Drive Requirement
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability

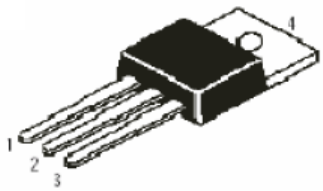


V_{DSS} = 650V

I_{D25} = 9.5A

$R_{DS(ON)}$ = 0.73 Ω

TO-220



Pin1–Gate
Pin2–Drain
Pin1–Source

Description

StarMOS is a new generation of high voltage N–Channel enhancement mode power MOSFETs. This new technology minimises the JFET effect, increases packing density and reduces the on-resistance. StarMOS also achieves faster switching speeds through optimised gate layout with planar stripe DMOS technology.

Application

- Switching application

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D@Tc=25℃	Continuous Drain Current,V_{GS}@10V	9.5	A
I_D@Tc=100℃	Continuous Drain Current,V_{GS}@10V	5.7	
I_{DM}	Pulsed Drain Current ①	38	
P_D@Tc=25℃	Power Dissipation	156	W
	Linear Derating Factor	1.25	W/℃
V_{GS}	Gate-to-Source Voltage	±30	V
E_{AS}	Single Pulse Avalanche Energy ②	700	mJ
I_{AR}	Avalanche Current ①	9.5	A
E_{AR}	Repetitive Avalanche Energy ①	15.6	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.5	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	- 55 to +150	℃
	Soldering Temperature, for 10 seconds	300(1.6mm from case)	
	Mounting Torque,6-32 or M3 screw	10 lbf•in(1.1N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case	—	—	0.8	℃/W
$R_{\theta CS}$	Case-to-Sink,Flat,Greased Surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	—	62.5	

Electrical Characteristics @T_J=25 ℃(unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	650	—	—	V	V_{GS}=0V,I_D=250μA
$\triangle V_{(BR)DSS}/\triangle T_J$	Breakdown Voltage Temp.Coefficient	—	0.7	—	V/℃	Reference to 25℃,I_D=250μA
$R_{DS(on)}$	Static Drain-to-Source On-resistance	—	0.6	0.73	Ω	V_{GS}=10V,I_D=4.75A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	V_{DS}=V_{GS},I_D=250μA
gfs	Forward Transconductance	—	8.0	—	S	V_{DS}=40V,I_D=4.75A
I_{DSS}	Drain-to-Source Leakage current	—	—	1	μA	V_{DS}=650V,V_{GS}=0V
		—	—	10		V_{DS}=480V,V_{GS}=0V,T_J=150℃
I_{GSS}	Gate-to-Source Forward leakage	—	—	100	nA	V_{GS}=30V
	Gate to Source Reverse leakage	—	—	100		V_{GS}= -30V
Qg	Total Gate Charge	—	44	57	nC	I_D=9.5A
Qgs	Gate-to-Source charge	—	6.7	—		V_{DS}=480V
Qgd	Gate-to-Drain("Miller") charge	—	18.5	—		V_{GS}=10V
td(on)	Turn-on Delay Time	—	23	55	nS	V_{DD}=300V
tr	Rise Time	—	69	150		I_D=9.5A
td(off)	Turn-Off Delay Time	—	144	300		R_G=25Ω
tf	Fall Time	—	77	165		
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm(0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
Ciss	Input Capacitance	—	1570	2040	pF	V_{GS}=0V
Coss	Output Capacitance	—	166	215		V_{DS}=25V
Crss	Reverse Transfer Capacitance	—	18	24		f=1.0MHz

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	9.5	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	38		
V_{SD}	Diode Forward Voltage	—	—	1.4	V	T_J=25℃,I_S=9.5A,V_{GS}=0V ④
trr	Reverse Recovery Time	—	420	—	nS	T_J=25℃,I_F=9.5A
Qrr	Reverse Recovery Charge	—	4.2		nC	di/dt=100A/μs ④
ton	Forward Turn-on Time	Intrinsic turn-on time is negligible (turn-on is dominated by Ls + L_D)				

Notes:

① Repetitive rating,pulse width limited by max.junction temperature

② L = 14.2mH, IAS =9.5 A, VDD = 50V, RG = 25 Ω, Starting TJ = 25°C

③ I_{SD}≤9.5A,di/dt≤200A/μS,V_{DD}≤$V_{(BR)DSS}$, T_J≤25℃

④ Pulse width≤300μS; duty cycle≤2%